

# 16-Mbit (1 M × 16 / 2 M × 8) Static RAM

## Features

- TSOP I package configurable as 1 M × 16 or 2 M × 8 SRAM
- Very high speed: 45 ns
- Temperature ranges
  - Industrial: -40 °C to +85 °C
  - Automotive-A: -40 °C to +85 °C
- Wide voltage range: 2.20 V to 3.60 V
- Ultra-low standby power
  - Typical standby current: 1.5 μA
  - Maximum standby current: 12 μA
- Ultra-low active power
  - Typical active current: 2.2 mA at f = 1 MHz
- Easy memory expansion with  $\overline{CE}_1$ ,  $CE_2$ , and  $\overline{OE}$  Features
- Automatic power-down when deselected
- CMOS for optimum speed and power
- Offered in Pb-free 48-ball VFBGA and 48-pin TSOP I packages

## Functional Description

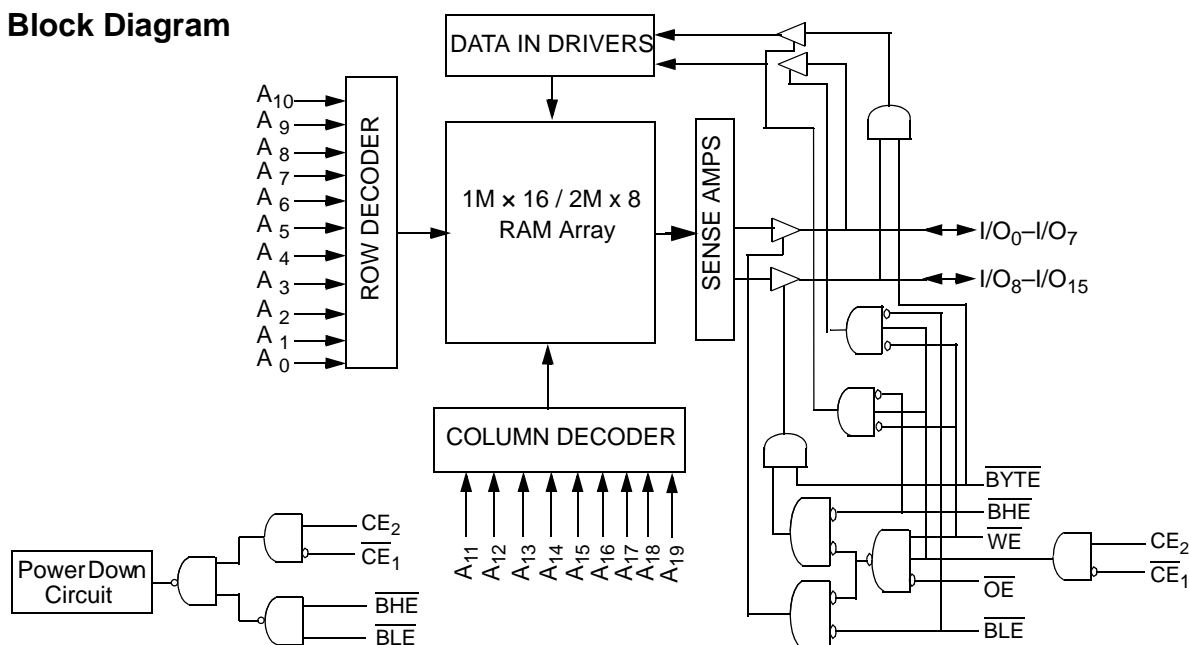
The CY62167EV30 is a high performance CMOS static RAM organized as 1M words by 16 bits or 2M words by 8 bits. This

device features an advanced circuit design that provides an ultra low active current. Ultra low active current is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that reduces power consumption by 99 percent when addresses are not toggling. Place the device into standby mode when deselected ( $\overline{CE}_1$  HIGH or  $CE_2$  LOW or both  $\overline{BHE}$  and  $\overline{BLE}$  are HIGH). The input and output pins ( $I/O_0$  through  $I/O_{15}$ ) are placed in a high impedance state when: the device is deselected ( $\overline{CE}_1$  HIGH or  $CE_2$  LOW), outputs are disabled ( $\overline{OE}$  HIGH), both Byte High Enable and Byte Low Enable are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH), or a write operation is in progress ( $\overline{CE}_1$  LOW,  $CE_2$  HIGH and  $\overline{WE}$  LOW).

To write to the device, take Chip Enables ( $\overline{CE}_1$  LOW and  $CE_2$  HIGH) and Write Enable ( $\overline{WE}$ ) input LOW. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from  $I/O$  pins ( $I/O_0$  through  $I/O_7$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{19}$ ). If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from the  $I/O$  pins ( $I/O_8$  through  $I/O_{15}$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{19}$ ).

To read from the device, take Chip Enables ( $\overline{CE}_1$  LOW and  $CE_2$  HIGH) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins appears on  $I/O_0$  to  $I/O_7$ . If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from memory appears on  $I/O_8$  to  $I/O_{15}$ . See [Truth Table on page 12](#) for a complete description of read and write modes.

## Logic Block Diagram



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## Pin Configuration

Figure 1. 48-ball VFBGA pinout (Top View) <sup>[1, 2]</sup>

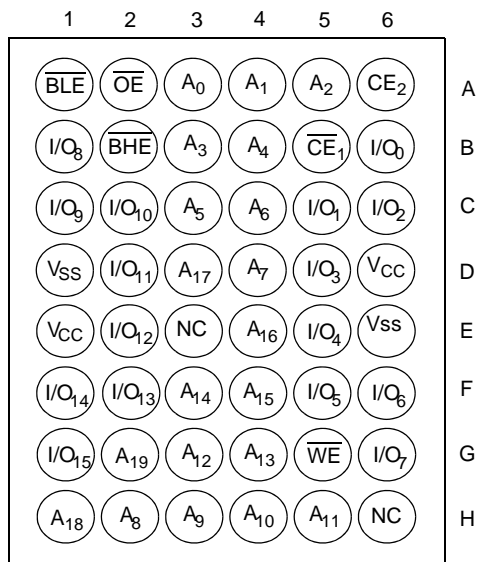


Figure 2. 48-pin TSOP I pinout (Top View) <sup>[2, 3]</sup>



## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V)			Speed (ns)	Power Dissipation					
						Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> (μA)	
						f = 1 MHz		f = f <sub>max</sub>			
		Min	Typ <sup>[4]</sup>	Max		Typ <sup>[4]</sup>	Max	Typ <sup>[4]</sup>	Max	Typ <sup>[4]</sup>	Max
CY62167EV30LL	Industrial / Automotive-A	2.2	3.0	3.6	45	2.2	4.0	25	30	1.5	12

### Notes

- Ball H6 for the VFBGA package can be used to upgrade to a 32M density.
- NC pins are not connected on the die.
- The BYTE pin in the 48-pin TSOP I package has to be tied to V<sub>CC</sub> to use the device as a 1 M x 16 SRAM. The 48-pin TSOP I package can also be used as a 2 M x 8 SRAM by tying the BYTE signal to V<sub>SS</sub>. In the 2 M x 8 configuration, Pin 45 is A20, while BHE, BLE and I/O<sub>8</sub> to I/O<sub>14</sub> pins are not used.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.

## Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... -65 °C to + 150 °C

Ambient temperature with power applied ..... -55 °C to + 125 °C

Supply voltage to ground potential ..... -0.3 V to 3.9 V ( $V_{CC(max)}$  + 0.3 V)

DC voltage applied to outputs in High Z state <sup>[5, 6]</sup> ..... -0.3 V to 3.9 V ( $V_{CC(max)}$  + 0.3 V)

DC input voltage <sup>[5, 6]</sup> ..... -0.3 V to 3.9 V ( $V_{CC(max)}$  + 0.3 V)

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... >2001 V

Latch-up current ..... >200 mA

## Operating Range

Device	Range	Ambient Temperature	$V_{CC}$ <sup>[7]</sup>
CY62167EV30LL	Industrial / Automotive-A	-40 °C to +85 °C	2.2 V to 3.6 V

## Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	45 ns (Industrial/Automotive-A)			Unit
			Min	Typ <sup>[8]</sup>	Max	
$V_{OH}$	Output HIGH voltage	$2.2 \leq V_{CC} \leq 2.7$ $I_{OH} = -0.1$ mA	2.0	—	—	V
		$2.7 \leq V_{CC} \leq 3.6$ $I_{OH} = -1.0$ mA	2.4	—	—	V
$V_{OL}$	Output LOW voltage	$2.2 \leq V_{CC} \leq 2.7$ $I_{OL} = 0.1$ mA	—	—	0.4	V
		$2.7 \leq V_{CC} \leq 3.6$ $I_{OL} = 2.1$ mA	—	—	0.4	V
$V_{IH}$	Input HIGH voltage	$2.2 \leq V_{CC} \leq 2.7$	1.8	—	$V_{CC} + 0.3$ V	V
		$2.7 \leq V_{CC} \leq 3.6$	2.2	—	$V_{CC} + 0.3$ V	V
$V_{IL}$	Input LOW voltage	$2.2 \leq V_{CC} \leq 2.7$	-0.3	—	0.6	V
		$2.7 \leq V_{CC} \leq 3.6$ For VFBGA package	-0.3	—	0.8	V
		$2.7 \leq V_{CC} \leq 3.6$ For TSOP I package	-0.3	—	0.7 <sup>[9]</sup>	V
$I_{IX}$	Input leakage current	$GND \leq V_I \leq V_{CC}$	-1	—	+1	μA
$I_{OZ}$	Output leakage current	$GND \leq V_O \leq V_{CC}$ , Output disabled	-1	—	+1	μA
$I_{CC}$	$V_{CC}$ operating supply current	$f = f_{max} = 1/t_{RC}$ $V_{CC} = V_{CC(max)}$	—	25	30	mA
		$f = 1$ MHz $I_{OUT} = 0$ mA CMOS levels	—	2.2	4.0	mA
$I_{SB1}$ <sup>[10]</sup>	Automatic power down current—CMOS inputs	$CE_1 \geq V_{CC} - 0.2$ V or $CE_2 \leq 0.2$ V or (BHE and BLE) $\geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V, $V_{IN} \leq 0.2$ V, $f = f_{max}$ (address and data only), $f = 0$ (OE, and WE), $V_{CC} = V_{CC(max)}$	—	1.5	12	μA
$I_{SB2}$ <sup>[10]</sup>	Automatic power down current—CMOS inputs	$CE_1 \geq V_{CC} - 0.2$ V or $CE_2 \leq 0.2$ V or (BHE and BLE) $\geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V, $f = 0$ , $V_{CC} = V_{CC(max)}$	—	1.5	12	μA

### Notes

- $V_{IL(min)}$  = -2.0 V for pulse durations less than 20 ns.
- $V_{IH(max)}$  =  $V_{CC} + 0.75$  V for pulse durations less than 20 ns.
- Full Device AC operation assumes a 100 μs ramp time from 0 to  $V_{CC(min)}$  and 200 μs wait time after  $V_{CC}$  stabilization.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25$  °C.
- Under DC conditions the device meets a  $V_{IL}$  of 0.8 V. However, in dynamic conditions Input LOW Voltage applied to the device must not be higher than 0.7 V. This is applicable to TSOP I package only.
- Chip enables ( $\overline{CE}_1$  and  $CE_2$ ), byte enables ( $\overline{BHE}$  and  $\overline{BLE}$ ) and  $\overline{BYTE}$  must be tied to CMOS levels to meet the  $I_{SB1}/I_{SB2} / I_{CCDR}$  spec. Other inputs can be left floating.

## Capacitance

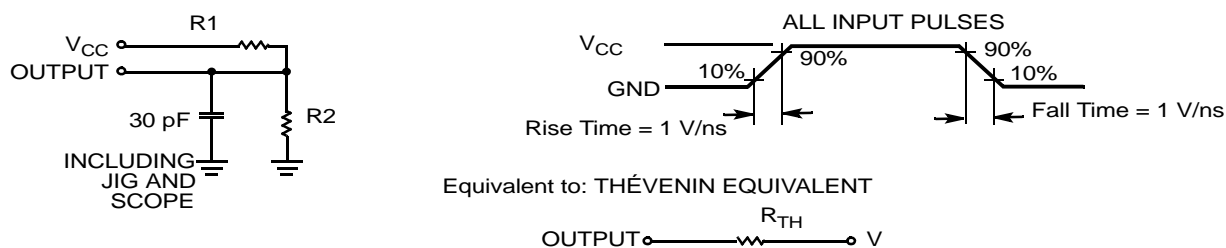
Parameter <sup>[11]</sup>	Description	Test Conditions	Max	Unit
$C_{IN}$	Input capacitance	$T_A = 25\text{ }^{\circ}\text{C}$ , $f = 1\text{ MHz}$ , $V_{CC} = V_{CC(typ)}$	10	pF
$C_{OUT}$	Output capacitance		10	pF

## Thermal Resistance

Parameter <sup>[11]</sup>	Description	Test Conditions	48-ball VFBGA	48-pin TSOP I	Unit
$\Theta_{JA}$	Thermal resistance (junction to ambient)	Still air, soldered on a 3 x 4.5 inch, two-layer printed circuit board	55	60	$^{\circ}\text{C/W}$
$\Theta_{JC}$	Thermal resistance (junction to case)		16	4.3	$^{\circ}\text{C/W}$

## AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms



Parameters	2.2 V to 2.7 V	2.7 V to 3.6 V	Unit
R1	16667	1103	$\Omega$
R2	15385	1554	$\Omega$
$R_{TH}$	8000	645	$\Omega$
$V_{TH}$	1.20	1.75	V

### Note

11. Tested initially and after any design or process changes that may affect these parameters.

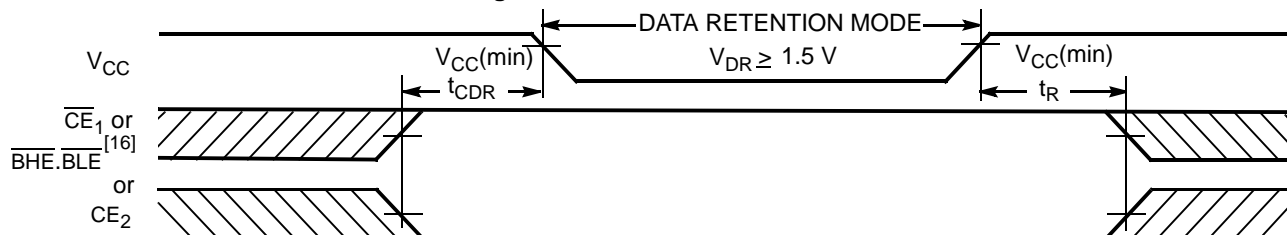
## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions			Min	Typ <sup>[12]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention				1.5	–	–	V
$I_{CCDR}^{[13]}$	Data retention current	$V_{CC} = 1.5\text{ V to }3.0\text{ V},$ $\overline{CE}_1 \geq V_{CC} - 0.2\text{ V or }CE_2 \leq 0.2\text{ V or}$ $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2\text{ V},$ $V_{IN} \geq V_{CC} - 0.2\text{ V or }V_{IN} \leq 0.2\text{ V}$	Industrial	48-pin TSOP I	–	–	8	$\mu\text{A}$
		$V_{CC} = 1.5\text{ V}, \overline{CE}_1 \geq V_{CC} - 0.2\text{ V or}$ $CE_2 \leq 0.2\text{ V or}$ $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2\text{ V},$ $V_{IN} \geq V_{CC} - 0.2\text{ V or }V_{IN} \leq 0.2\text{ V}$	Industrial	Other packages	–	–	10	$\mu\text{A}$
			Automotive-A	All packages	–	–	10	$\mu\text{A}$
$t_{CDR}^{[14]}$	Chip deselect to data retention time				0	–	–	–
$t_R^{[15]}$	Operation recovery time				45	–	–	ns

## Data Retention Waveform

Figure 4. Data Retention Waveform



### Notes

12. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25\text{ }^\circ\text{C}$ .
13. Chip enables ( $\overline{CE}_1$  and  $CE_2$ ), byte enables ( $\overline{BHE}$  and  $\overline{BLE}$ ) and  $\overline{BYTE}$  must be tied to CMOS levels to meet the  $I_{SB1}/I_{SB2}/I_{CCDR}$  spec. Other inputs can be left floating.
14. Tested initially and after any design or process changes that may affect these parameters.
15. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$  or stable at  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$ .
16.  $\overline{BHE.BLE}$  is the AND of both  $\overline{BHE}$  and  $\overline{BLE}$ . Deselect the chip by either disabling the chip enable signals or by disabling both  $\overline{BHE}$  and  $\overline{BLE}$ .

## Switching Characteristics

Parameter <sup>[17, 18]</sup>	Description	45 ns (Industrial / Automotive-A)		Unit
		Min	Max	
READ CYCLE				
t <sub>RC</sub>	Read cycle time	45	–	ns
t <sub>AA</sub>	Address to data valid	–	45	ns
t <sub>OHA</sub>	Data hold from address change	10	–	ns
t <sub>ACE</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to data valid	–	45	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to data valid	–	22	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[19]</sup>	5	–	ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[19, 20]</sup>	–	18	ns
t <sub>LZCE</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to Low Z <sup>[19]</sup>	10	–	ns
t <sub>HZCE</sub>	$\overline{CE}_1$ HIGH and CE <sub>2</sub> LOW to High Z <sup>[19, 20]</sup>	–	18	ns
t <sub>PU</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to power-up	0	–	ns
t <sub>PD</sub>	$\overline{CE}_1$ HIGH and CE <sub>2</sub> LOW to power-down	–	45	ns
t <sub>DBE</sub>	BLE / BHE LOW to data valid	–	45	ns
t <sub>LZBE</sub>	$\overline{BLE} / \overline{BHE}$ LOW to Low Z <sup>[19]</sup>	10	–	ns
t <sub>HZBE</sub>	$\overline{BLE} / \overline{BHE}$ HIGH to High Z <sup>[19, 20]</sup>	–	18	ns
WRITE CYCLE <sup>[21]</sup>				
t <sub>WC</sub>	Write cycle time	45	–	ns
t <sub>SCE</sub>	$\overline{CE}_1$ LOW and CE <sub>2</sub> HIGH to write end	35	–	ns
t <sub>AW</sub>	Address setup to write end	35	–	ns
t <sub>HA</sub>	Address hold from write end	0	–	ns
t <sub>SA</sub>	Address setup to write start	0	–	ns
t <sub>PWE</sub>	$\overline{WE}$ pulse width	35	–	ns
t <sub>BW</sub>	$\overline{BLE} / \overline{BHE}$ LOW to write end	35	–	ns
t <sub>SD</sub>	Data setup to write end	25	–	ns
t <sub>HD</sub>	Data hold from write end	0	–	ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>[19, 20]</sup>	–	18	ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>[19]</sup>	10	–	ns

### Notes

17. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1 V/ns, timing reference levels of  $V_{CC(typ)}/2$ , input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in [Figure 3 on page 5](#).

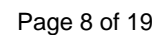
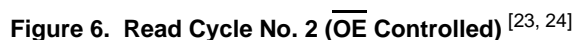
18. In an earlier revision of this device, under a specific application condition, READ and WRITE operations were limited to switching of the byte enable and/or chip enable signals as described in the Application Notes [AN13842](#) and [AN66311](#). However, the issue has been fixed and in production now, and hence, these Application Notes are no longer applicable. They are available for download on our website as they contain information on the date code of the parts, beyond which the fix has been in production.

19. At any temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZBE}$  is less than  $t_{LZBE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any device.

20.  $t_{HZOE}$ ,  $t_{HZCE}$ ,  $t_{HZBE}$ , and  $t_{HZWE}$  transitions are measured when the outputs enter a high impedance state.

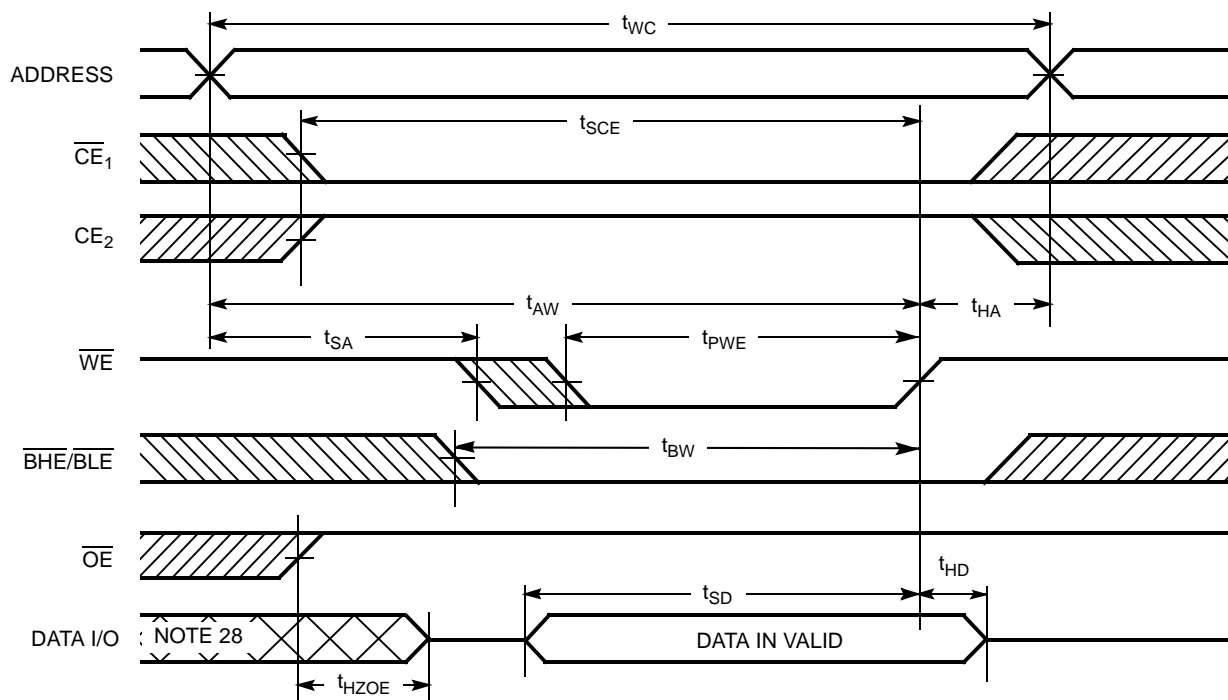
21. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE}_1 = V_{IL}$ ,  $\overline{BHE}$  or  $\overline{BLE}$  or both =  $V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

**Figure 5. Read Cycle No. 1 (Address Transition Controlled)** [22, 23]





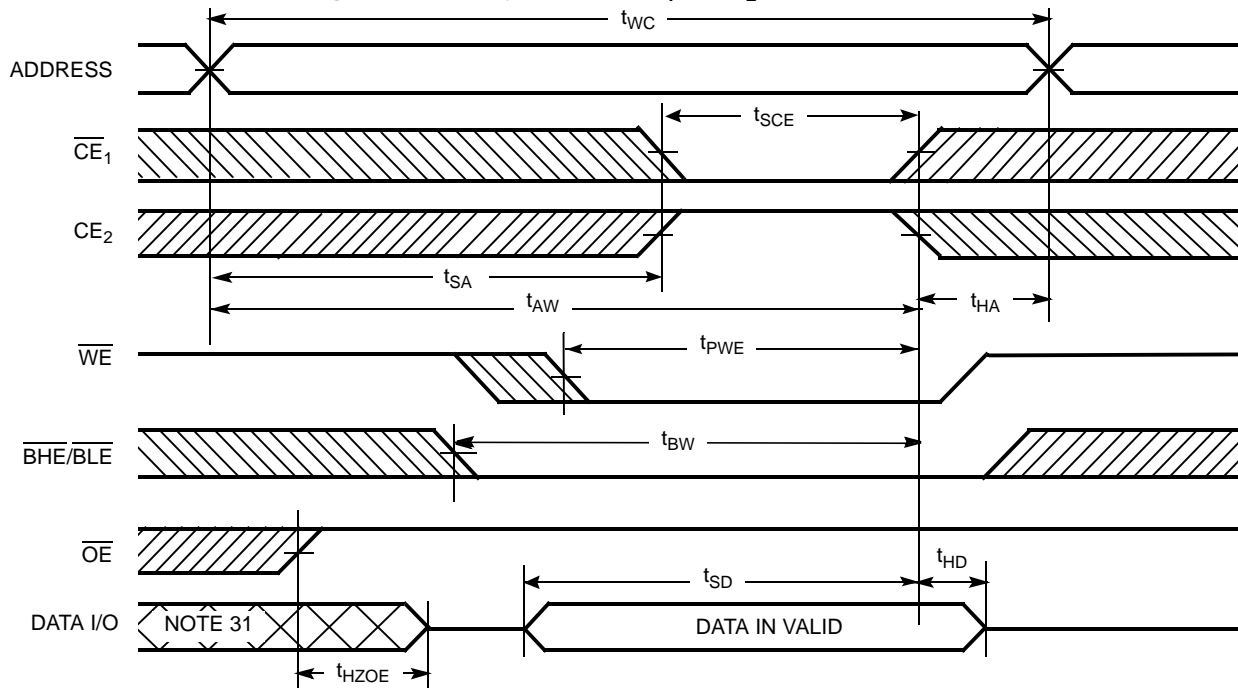
**Switching Waveforms** (continued)

**Figure 7. Write Cycle No. 1 ( $\overline{\text{WE}}$  Controlled)** [25, 26, 27]

**Notes**

25. The internal write time of the memory is defined by the overlap of  $\overline{\text{WE}}$ ,  $\overline{\text{CE}}_1 = V_{\text{IL}}$ ,  $\overline{\text{BHE}}$  or  $\overline{\text{BLE}}$  or both =  $V_{\text{IL}}$ , and  $\text{CE}_2 = V_{\text{IH}}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
26. Data I/O is high impedance if  $\overline{\text{OE}} = V_{\text{IH}}$ .
27. If  $\overline{\text{CE}}_1$  goes HIGH and  $\text{CE}_2$  goes LOW simultaneously with  $\overline{\text{WE}} = V_{\text{IH}}$ , the output remains in a high impedance state.
28. During this period the I/Os are in output state. Do not apply input signals.

## Switching Waveforms (continued)

**Figure 8. Write Cycle No. 2 ( $\overline{CE_1}$  or  $CE_2$  Controlled) [29, 30]**



### Notes

29. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE_1} = V_{IL}$ ,  $\overline{BHE}$  or  $\overline{BLE}$  or both =  $V_{IL}$ , and  $CE_2 = V_{IH}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
30. If  $\overline{CE_1}$  goes HIGH and  $CE_2$  goes LOW simultaneously with  $\overline{WE} = V_{IH}$ , the output remains in a high impedance state.
31. During this period the I/Os are in output state. Do not apply input signals.

## Switching Waveforms (continued)

Figure 9. Write Cycle No. 3 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) <sup>[32]</sup>

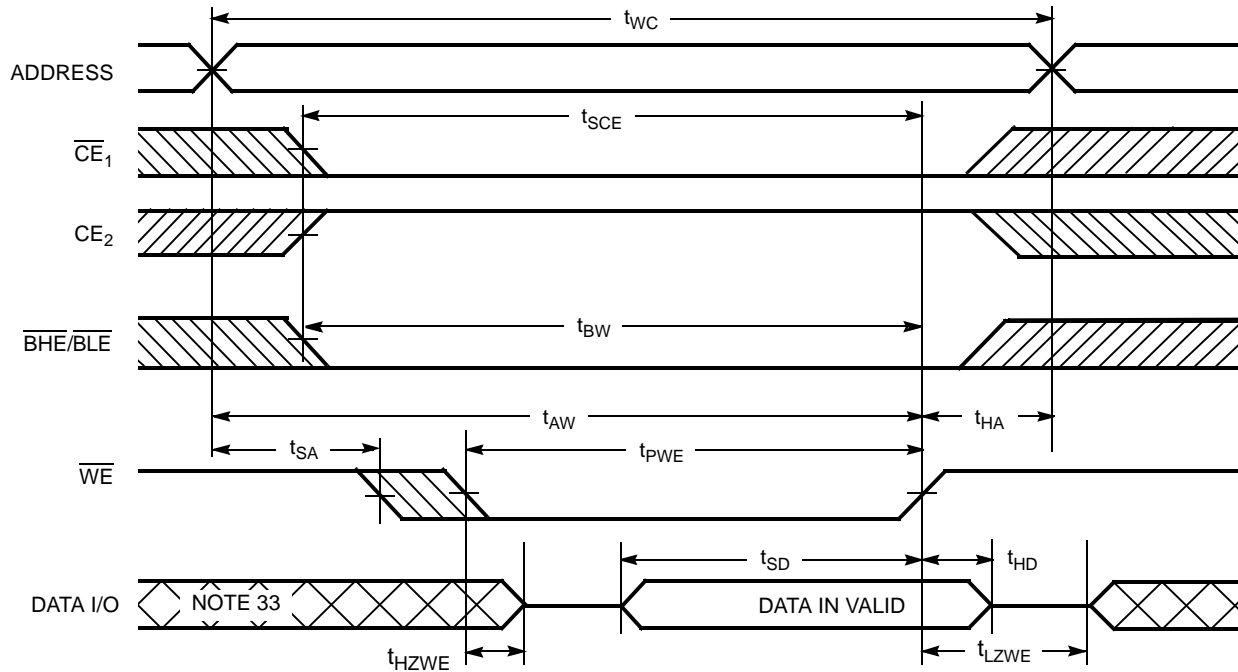
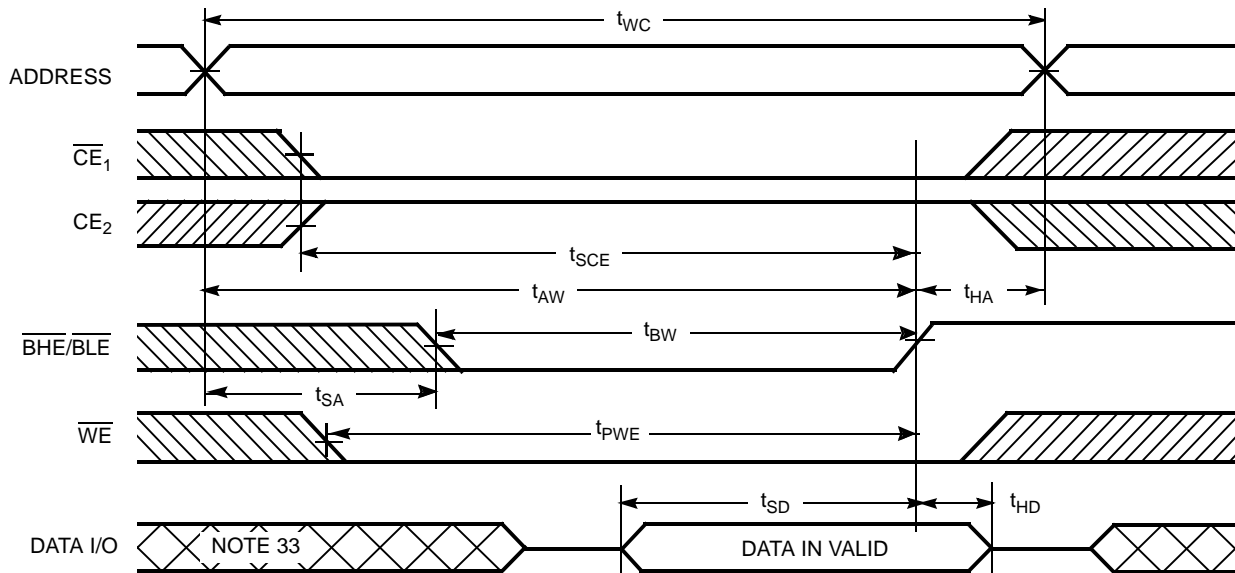


Figure 10. Write Cycle No. 4 ( $\overline{BHE/BLER}$  controlled,  $\overline{OE}$  LOW) <sup>[32]</sup>



### Notes

32. If  $\overline{CE}_1$  goes HIGH and  $\overline{CE}_2$  goes LOW simultaneously with  $\overline{WE} = V_{IH}$ , the output remains in a high impedance state.  
33. During this period the I/Os are in output state. Do not apply input signals.

**Truth Table**

$\overline{CE}_1$	$\overline{CE}_2$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X <sup>[34]</sup>	X	X	X <sup>[34]</sup>	X <sup>[34]</sup>	High Z	Deselect/Power-down	Standby ( $I_{SB}$ )
X <sup>[34]</sup>	L	X	X	X <sup>[34]</sup>	X <sup>[34]</sup>	High Z	Deselect/Power-down	Standby ( $I_{SB}$ )
X <sup>[34]</sup>	X <sup>[34]</sup>	X	X	H	H	High Z	Deselect/Power-down	Standby ( $I_{SB}$ )
L	H	H	L	L	L	Data Out ( $I/O_0$ – $I/O_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	H	L	H	L	Data Out ( $I/O_0$ – $I/O_7$ ); High Z ( $I/O_8$ – $I/O_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	H	L	L	H	High Z ( $I/O_0$ – $I/O_7$ ); Data Out ( $I/O_8$ – $I/O_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	H	H	L	H	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	H	H	H	L	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	H	H	L	L	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	L	X	L	L	Data In ( $I/O_0$ – $I/O_{15}$ )	Write	Active ( $I_{CC}$ )
L	H	L	X	H	L	Data In ( $I/O_0$ – $I/O_7$ ); High Z ( $I/O_8$ – $I/O_{15}$ )	Write	Active ( $I_{CC}$ )
L	H	L	X	L	H	High Z ( $I/O_0$ – $I/O_7$ ); Data In ( $I/O_8$ – $I/O_{15}$ )	Write	Active ( $I_{CC}$ )

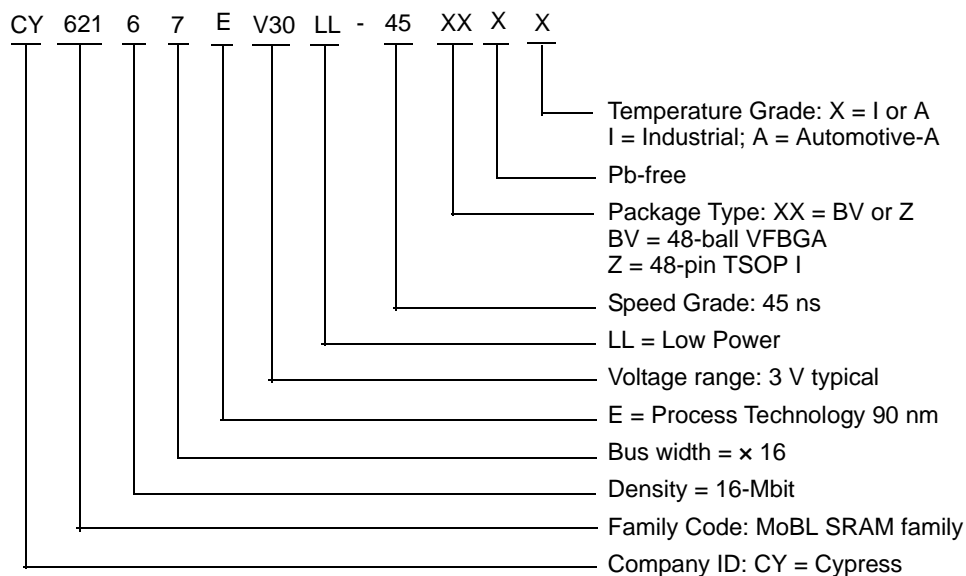
**Note**

34. The 'X' (Don't care) state for the chip enables and Byte enables in the truth table refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

## Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62167EV30LL-45BVI	51-85150	48-ball VFBGA (6 × 8 × 1 mm), Package Code: BV48	Industrial
	CY62167EV30LL-45BVXI	51-85150	48-ball VFBGA (6 × 8 × 1 mm) (Pb-free), Package Code: BZ48	
	CY62167EV30LL-45ZXI	51-85183	48-pin TSOP I (Pb-free)	
	CY62167EV30LL-45BVXA	51-85150	48-ball VFBGA (6 × 8 × 1 mm) (Pb-free), Package Code: BZ48	Automotive-A
	CY62167EV30LL-45ZXA	51-85183	48-pin TSOP I (Pb-free)	

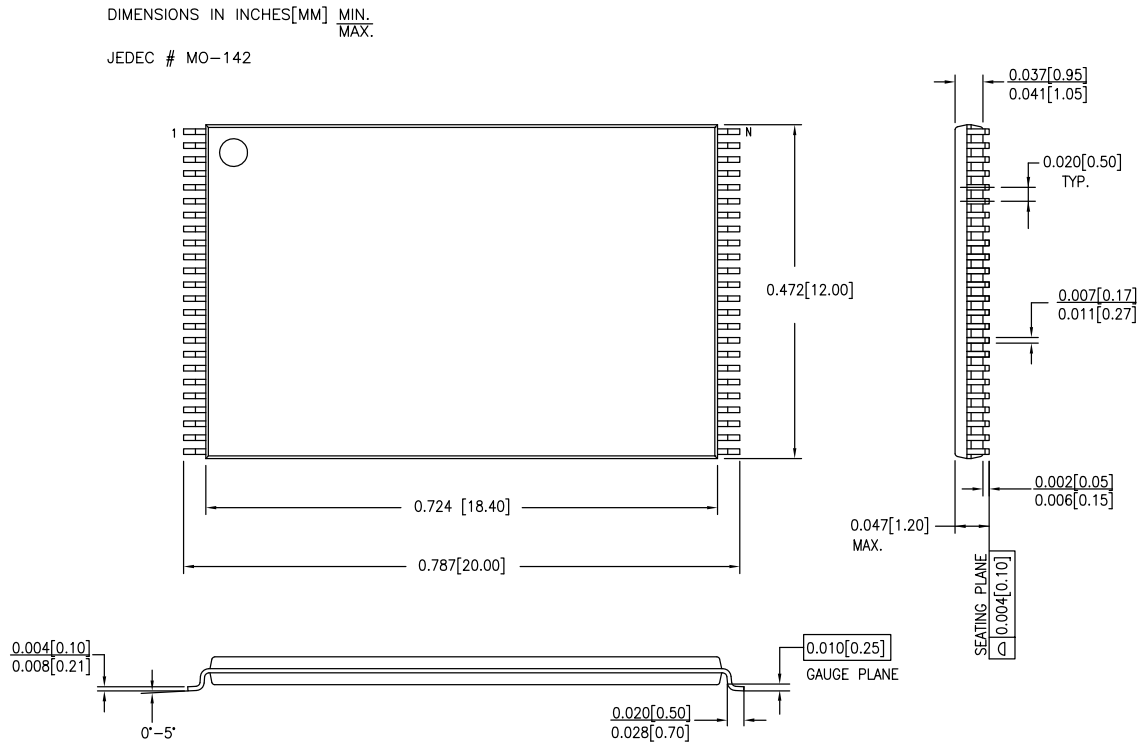
## Ordering Code Definitions





**Package Diagrams** (continued)

**Figure 12. 48-pin TSOP I (12 × 18.4 × 1.0 mm) Z48A Package Outline, 51-85183**



51-85183 \*C

## Acronyms

Acronym	Description
BHE	byte high enable
BLE	byte low enable
CE	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
OE	output enable
SRAM	static random access memory
TSOP	thin small outline package
VFBGA	very fine-pitch ball grid array
WE	write enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt



## Document History Page

Document Title: CY62167EV30 MoBL®, 16-Mbit (1 M × 16 / 2 M × 8) Static RAM Document Number: 38-05446				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	202600	AJU	01/23/2004	New data sheet.
*A	463674	NXR	See ECN	<p>Changed status from Advance Information to Preliminary</p> <p>Removed 'L' bin and 35 ns speed bin from product offering</p> <p>Modified Data sheet to include x8 configurability.</p> <p>Changed ball E3 in FBGA pinout from DNU to NC</p> <p>Changed the <math>I_{SB2(Typ)}</math> value from 1.3 <math>\mu A</math> to 1.5 <math>\mu A</math></p> <p>Changed the <math>I_{CC(Max)}</math> value from 40 mA to 25 mA</p> <p>Changed Vcc stabilization time in footnote #9 from 100 <math>\mu s</math> to 200 <math>\mu s</math></p> <p>Changed the AC Test Load Capacitance value from 50 pF to 30 pF</p> <p>Corrected typo in Data Retention Characteristics (<math>t_R</math>) from 100 <math>\mu s</math> to <math>t_{RC}</math> ns</p> <p>Changed <math>t_{OHA}</math>, <math>t_{LZCE}</math>, <math>t_{LZBE}</math>, and <math>t_{LZWE}</math> from 6 ns to 10 ns</p> <p>Changed <math>t_{LZOE}</math> from 3 ns to 5 ns.</p> <p>Changed <math>t_{HZOE}</math>, <math>t_{HZCE}</math>, <math>t_{HZBE}</math>, and <math>t_{HZWE}</math> from 15 ns to 18 ns</p> <p>Changed <math>t_{SCE}</math>, <math>t_{AW}</math>, and <math>t_{BW}</math> from 40 ns to 35 ns</p> <p>Changed <math>t_{PE}</math> from 30 ns to 35 ns</p> <p>Changed <math>t_{SD}</math> from 20 ns to 25 ns</p> <p>Updated 48-ball FBGA Package Information.</p> <p>Updated the Ordering Information table</p>
*B	469169	NSI	See ECN	Minor Change: Moved to external web
*C	1130323	VKN	See ECN	<p>Changed status from Preliminary to Final.</p> <p>Changed <math>I_{CC}</math> max spec from 2.8 mA to 4.0 mA for <math>f = 1\text{MHz}</math></p> <p>Changed <math>I_{CC}</math> typ spec from 22 mA to 25 mA for <math>f = f_{max}</math></p> <p>Changed <math>I_{CC}</math> max spec from 25 mA to 30 mA for <math>f = f_{max}</math></p> <p>Added <math>V_{IL}</math> spec for TSOP I package and footnote# 9</p> <p>Added footnote# 10 related to <math>I_{SB2}</math> and <math>I_{CCDR}</math></p> <p>Changed <math>I_{SB1}</math> and <math>I_{SB2}</math> spec from 8.5 <math>\mu A</math> to 12 <math>\mu A</math></p> <p>Changed <math>I_{CCDR}</math> spec from 8 <math>\mu A</math> to 10 <math>\mu A</math></p> <p>Added footnote# 15 related to AC timing parameters</p>
*D	1323984	VKN / AESA	See ECN	<p>Modified <math>I_{CCDR}</math> spec for TSOP I package</p> <p>Added 48-ball VFBGA (6 × 7 × 1mm) package</p> <p>Added footnote# 1 related to VFBGA (6 × 7 × 1mm) package</p> <p>Updated Ordering Information table</p>
*E	2678799	VKN / PYRS	03/25/2009	Added Automotive-A information
*F	2720234	VKN / AESA	06/17/2009	Included -45BVXA part in the Ordering information table
*G	2880574	VKN	02/18/2010	<p>Modified <math>I_{CCDR}</math> spec from 8 <math>\mu A</math> to 10 <math>\mu A</math> for Auto-A grade.</p> <p>Added <a href="#">Contents</a>.</p> <p>Updated all package diagrams.</p> <p>Updated links in <a href="#">Sales</a>, <a href="#">Solutions</a>, and <a href="#">Legal Information</a>.</p>
*H	2934396	VKN	06/03/10	<p>Added footnote #25 related to chip enable.</p> <p>Updated template.</p>
*I	3006301	RAME	08/12/2010	<p>Included BHE and BLE in <math>I_{SB1}</math>, <math>I_{SB2}</math>, and <math>I_{CCDR}</math> test conditions to reflect Byte power down feature.</p> <p>Removed 48-ball VFBGA (6 × 7 × 1 mm) package related information.</p> <p>Added Acronyms and Ordering code definition.</p> <p>Format updates to match template.</p>

**Document History Page** (continued)

Document Title: CY62167EV30 MoBL®, 16-Mbit (1 M × 16 / 2 M × 8) Static RAM Document Number: 38-05446				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*J	3295175	RAME	06/29/2011	Updated <a href="#">Package Diagrams</a> . Added <a href="#">Document Conventions</a> . Removed reference to AN1064 SRAM system guidelines. Added I <sub>SB1</sub> to footnotes <a href="#">10</a> and <a href="#">13</a> . Added byte enables to footnote <a href="#">34</a> and referenced to Truth table.
*K	3411301	TAVA	10/17/2011	Updated <a href="#">Switching Waveforms</a> . Updated <a href="#">Package Diagrams</a> . Updated in new template.
*L	3667939	TAVA	07/09/2012	Updated <a href="#">Ordering Information</a> (No change in part numbers, updated details in Package Type column only). Updated <a href="#">Package Diagrams</a> (Spec 51-85150 (Updated figure caption only, no change in revision)).
*M	4102969	VINI	08/23/2013	Updated <a href="#">Switching Characteristics</a> : Updated Note 18.  Updated <a href="#">Package Diagrams</a> : spec 51-85150 – Changed revision from *G to *H.  Updated in new template.  Completing Sunset Review.

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